(H01L) L1(1)

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	H01L 23/12	→ (51)	H01L 23/053
•	H01L 23/14	→ (51)	H05K 1/02
	H01L 23/29	→ (51)	H01L 23/053
-	H01L 23/34	→ (51)	H01L 23/053
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- (74) Poulin, Gérard, BREVALEX 3, rue du Docteur Lancereaux, 75008 Parls, FR

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- (71) ATMEL CORPORATION, 2325 Orchard Parkway, San Jose, California 95131, US
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- (74) Käck, Jürgen, Kahler Käck Mollekopf Vorderer Anger 239, 86899 Landsberg/Lech, DE

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- (71) Solibro AB, Ultuna, 756 51 Uppsala, SE
- STOLT, Lars, S-755 91 Uppsala, SE KESSLER, John, F-44000 Nantes, FR
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- (71) Hong-Yuan Technology Co., Ltd., 3 Fl., No. 1, Alley 16 Lane 305, Zhonghe Road, Yonghe City, Taipei County, Talwan 234, TW
- (72) WU, Yu-Chao, Talwan 234, CN CHENG, Wei-Yuan, Taipei County Taiwan 241, CN
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- (71) Epivalley Co., Ltd., 51-2, Neungpycong-ri, Opoeup, Kwangju-si, Kyunggi-do 464-892, KR
- PARK, Joongseo 606-103, Samsung Raemian, Yangin-si, Kyunggi-do 449-564, KR
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